

Hasan Hseyin Gll

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70
papers

487
citations

12
h-index

17
g-index

73
ext. papers

601
ext. citations

2.3
avg, IF

4.71
L-index

#	Paper	IF	Citations
70	Electrical properties of Al/PCBM:ZnO/p-Si heterojunction for photodiode application. <i>Journal of Alloys and Compounds</i> , 2020 , 827, 154279	5.7	40
69	Study on the electrical properties of ZnSe/Si heterojunction diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 17806-17815	2.1	23
68	Device behavior of an In/p-Ag(Ga,In)Te ₂ /n-Si/Ag heterojunction diode. <i>Materials Science in Semiconductor Processing</i> , 2015 , 34, 138-145	4.3	22
67	Structural and temperature-dependent optical properties of thermally evaporated CdS thin films. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 148-152	4.3	21
66	Temperature-Dependent Electrical Characteristics of Au/Si ₃ N ₄ /4H n-SiC MIS Diode. <i>Journal of Electronic Materials</i> , 2018 , 47, 2979-2987	1.9	19
65	Dark and illuminated electrical characteristics of Si-based photodiode interlayered with CuCo ₅ S ₈ nanocrystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 935-948	2.1	18
64	Analysis of current conduction mechanism in CZTSSe/n-Si structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 5264-5274	2.1	17
63	Temperature dependence of band gaps in sputtered SnSe thin films. <i>Journal of Physics and Chemistry of Solids</i> , 2019 , 131, 22-26	3.9	16
62	Determination of current transport characteristics in Au-Cu/CuO/n-Si Schottky diodes. <i>Physica B: Condensed Matter</i> , 2019 , 570, 246-253	2.8	15
61	Analysis of forward and reverse biased current-voltage characteristics of Al/Al ₂ O ₃ /n-Si Schottky diode with atomic layer deposited Al ₂ O ₃ thin film interlayer. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 19383-19393	2.1	14
60	Deposition of CZTSe thin films and illumination effects on the device properties of Ag/n-Si/p-CZTSe/In heterostructure. <i>Journal of Alloys and Compounds</i> , 2017 , 709, 337-343	5.7	13
59	Investigation of structural, electronic, magnetic and lattice dynamical properties for XCoBi (X: Ti, Zr, Hf) Half-Heusler compounds. <i>Physica B: Condensed Matter</i> , 2020 , 587, 412146	2.8	13
58	Temperature and frequency effects on electrical and dielectric properties of n-4H SiC based metal-insulator-semiconductor (MIS) diode interlayered with Si ₃ N ₄ thin film. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 8705-8717	2.1	12
57	Investigation of electrical characteristics of Ag/ZnO/Si sandwich structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 15371-15378	2.1	11
56	Synthesis and temperature-tuned band gap characteristics of magnetron sputtered ZnTe thin films. <i>Physica B: Condensed Matter</i> , 2020 , 582, 411968	2.8	11
55	Temperature dependence of electrical properties in (In/Cu) ₂ (ZnSnTe) ₄ (Si/Ag diodes). <i>Bulletin of Materials Science</i> , 2019 , 42, 1	1.7	11
54	First principles study on the structural, electronic, mechanical and lattice dynamical properties of XRhSb (X = Ti and Zr) paramagnet half-Heusler antimonides. <i>Materials Research Express</i> , 2019 , 6, 106315 ¹⁻⁷	1.7	10

53	Enhanced diode performance in cadmium telluride/silicon nanowire heterostructures. <i>Journal of Alloys and Compounds</i> , 2015 , 644, 131-139	5.7	10
52	Structural and optical properties of ZnInTe thin films deposited by thermal evaporation technique. <i>Journal of Alloys and Compounds</i> , 2013 , 566, 83-89	5.7	10
51	Investigation of carrier transport mechanisms in the CuZnSe based hetero-structure grown by sputtering technique. <i>Canadian Journal of Physics</i> , 2018 , 96, 816-825	1.1	9
50	Investigation of precursor sequence and post-annealing effects on the properties of Cu ₂ SnZnSe ₄ thin films deposited by the elemental thermal evaporation. <i>Materials Research Express</i> , 2017 , 4, 086411	1.7	9
49	Optical and electrical characteristics of thermally evaporated Cu _{0.5} Ag _{0.5} InSe ₂ thin films. <i>Thin Solid Films</i> , 2017 , 639, 29-35	2.2	9
48	Frequency effect on electrical and dielectric characteristics of HfO ₂ -interlayered Si-based Schottky barrier diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 9394-9407	2.1	8
47	Device Characterization of ZnInSe ₂ Thin Films. <i>Energy Procedia</i> , 2016 , 102, 110-120	2.3	8
46	Investigation of electrical properties of (In/ZnIn) ₂ Te ₄ /n-Si/Ag diode. <i>Bulletin of Materials Science</i> , 2019 , 42, 1	1.7	7
45	Frequency effect on electrical and dielectric characteristics of In/Cu ₂ ZnSnTe ₄ /Si/Ag diode structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 9814-9821	2.1	7
44	Improved diode properties in zinc telluride thin film-silicon nanowire heterojunctions. <i>Philosophical Magazine</i> , 2015 , 95, 1164-1183	1.6	7
43	Electrical characterization of CdZnTe/Si diode structure. <i>Applied Physics A: Materials Science and Processing</i> , 2020 , 126, 1	2.6	7
42	CZTSSe thin films fabricated by single step deposition for superstrate solar cell applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 11301-11306	2.1	6
41	Investigations of thermal annealing role on the optical properties of Zn-In-Se thin films. <i>Optik</i> , 2017 , 144, 603-612	2.5	6
40	Electrical characteristics of organic heterojunction with an alternating benzotriazole and fluorene containing copolymer. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 18816-18831	2.1	6
39	Structural characteristics of thermally evaporated Cu _{0.5} Ag _{0.5} InSe ₂ thin films. <i>Materials Research Express</i> , 2016 , 3, 055901	1.7	6
38	Structural characterization of ZnInSe thin films. <i>Modern Physics Letters B</i> , 2017 , 31, 1750043	1.6	5
37	Temperature dependence of electrical properties in Cu _{0.5} Ag _{0.5} InSe ₂ /Si heterostructure. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 11258-11264	2.1	5
36	Characterization of Co-evaporated Cu-Ag-In-Se Thin Films. <i>Brazilian Journal of Physics</i> , 2014 , 44, 719-725	1.2	5

35	Construction of self-assembled vertical nanoflakes on CZTSSe thin films. <i>Materials Research Express</i> , 2019 , 6, 026421	1.7	5
34	Effects of Si nanowire on the device properties of n-ZnSe/p-Si heterostructure. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 4760-4765	2.1	4
33	Study on the Structural and Electrical Properties of Sequentially Deposited AgGaInTe Thin Films. <i>Journal of Low Temperature Physics</i> , 2015 , 178, 162-173	1.3	4
32	Investigation of band gap energy versus temperature for SnS ₂ thin films grown by RF-magnetron sputtering. <i>Physica B: Condensed Matter</i> , 2020 , 591, 412264	2.8	4
31	Structural and optical properties of thermally evaporated Cu-Ga-S (CGS) thin films. <i>Physica B: Condensed Matter</i> , 2018 , 547, 92-96	2.8	4
30	THz probe studies of MBE grown epitaxial GaAs. <i>Journal of Physics: Conference Series</i> , 2009 , 193, 012088	0.3	4
29	Analysis of temperature-dependent forward and leakage conduction mechanisms in organic thin film heterojunction diode with fluorine-based PCBM blend. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 15233-15242	2.1	4
28	Temperature-dependent optical characteristics of sputtered Ga-doped ZnO thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021 , 263, 114834	3.1	4
27	Optical band gap and dispersion of optical constants of Cu-Ga-S thin films. <i>Optik</i> , 2019 , 186, 147-154	2.5	3
26	Influence of temperature on optical properties of electron-beam-evaporated ZnSe thin film. <i>Physica Scripta</i> , 2020 , 95, 075804	2.6	3
25	Investigation of optical parameters of thermally evaporated ZnSe thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 1224-1228		3
24	Investigation of structural and optical parameters of CuAgInSe thin films deposited by thermal evaporation method. <i>Optik</i> , 2015 , 126, 1578-1583	2.5	3
23	Capacitance, conductance, and dielectric characteristics of Al/TiO ₂ /Si diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2021 , 32, 13549-13567	2.1	3
22	Temperature effects on optical characteristics of CdSe thin films. <i>Materials Science in Semiconductor Processing</i> , 2021 , 123, 105559	4.3	3
21	Material and Si-based diode analyses of sputtered ZnTe thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 11390-11397	2.1	2
20	FABRICATION AND CHARACTERIZATION OF TiO ₂ THIN FILM FOR DEVICE APPLICATIONS. <i>Surface Review and Letters</i> , 2019 , 26, 1850205	1.1	2
19	Device application of AgGa _{0.5} In _{0.5} Se ₂ thin films deposited by thermal sequential stacked layer method. <i>Materials Research Express</i> , 2014 , 1, 046407	1.7	2
18	Enhancement in Photovoltaic Characteristics of CdS/CdTe Heterojunction. <i>Journal of Polytechnic</i> , 801-805		2

17	Material and device properties of Si-based Cu _{0.5} Ag _{0.5} InSe ₂ thin-film heterojunction diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 1566-1573	2.1	2
16	Electrical Characterization of ZnInSe ₂ /Cu _{0.5} Ag _{0.5} InSe ₂ Thin-Film Heterojunction. <i>Journal of Electronic Materials</i> , 2019 , 48, 3096-3104	1.9	2
15	INVESTIGATION OF CONDUCTIVITY CHARACTERISTICS OF ZnInSe THIN FILMS. <i>Surface Review and Letters</i> , 2020 , 27, 1950083	1.1	2
14	First-principles studies of Tin+1SiNn (n = 1, 2, 3) MAX phase. <i>Philosophical Magazine</i> , 2020 , 100, 2183-2204	1.6	1
13	Temperature-dependent optical and electrical characterization of Cu-Ga-S thin films and their diode characteristics on n-Si. <i>Optik</i> , 2020 , 208, 164485	2.5	1
12	INVESTIGATION ON DEVICE CHARACTERISTICS OF n-CdS/p-Ag(Ga-In)Te ₂ HETEROJUNCTION DIODE. <i>Surface Review and Letters</i> , 2018 , 25, 1850107	1.1	1
11	Investigation of post-thermal annealing on material properties of CuInZnSe thin films. <i>Journal of Semiconductors</i> , 2017 , 38, 123001	2.3	1
10	Material characterization of thermally evaporated ZnSn ₂ Te ₄ thin films. <i>Optik</i> , 2019 , 178, 45-50	2.5	1
9	Optical and Nanomechanical Properties of Ga ₂ Se ₃ Single Crystals and Thin Films. <i>Jom</i> , 2021 , 73, 558-565	2.1	1
8	Temperature-dependent material characterization of CuZnSe ₂ thin films. <i>Thin Solid Films</i> , 2020 , 701, 137941	2.2	0
7	Effect of TiO ₂ Thin Film with Different Dopants in Bringing Au-Metal into a Contact with n-Si. <i>Journal of Inorganic and Organometallic Polymers and Materials</i> , 2022 , 32, 1067	3.2	0
6	Improvement of electrical characteristics of SnSe/Si heterostructure by integration of Si nanowires. <i>Physica B: Condensed Matter</i> , 2021 , 604, 412669	2.8	0
5	Fabrication of CdSexTe _{1-x} thin films by sequential growth using double sources. <i>Physica B: Condensed Matter</i> , 2021 , 619, 413232	2.8	0
4	Analysis of temperature-dependent transmittance spectra of Zn _{0.5} In _{0.5} Se (ZIS) thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 9356-9362	2.1	
3	Structural and optical properties of thermally evaporated GaInSe thin films. <i>Modern Physics Letters B</i> , 2014 , 28, 1450101	1.6	
2	Annealing Effect on Dark Electrical Conductivity and Photoconductivity of Ga-In-Se Thin Films. <i>Acta Physica Polonica A</i> , 2018 , 133, 1119-1124	0.6	
1	Influence of the Spot Size of the Probe Beam on the Detected THz Power Using Electro-Optic Detection Method. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , 2011 , 107-111	0.2	